

Attorney Docket No. 24061.37/TSMC2002-1305  
Customer No. 27683

a second interconnect located over the dielectric layer, coupled to the second electrode by a third electrode by a third via, and coupled to the transistor contact by a fourth via.

20. The semiconductor device recited in Claim 19 wherein the first interconnect and the first and second vias are collectively a dual-damascene structure.

21. The semiconductor device recited in Claim 19 wherein the second interconnect and the third and fourth vias are collectively a dual-damascene structure.

22. The semiconductor device recited in Claim 19 wherein the first insulating layer includes an insulation layer and an etch stop layer located over the insulation layer.

23. The semiconductor device recited in Claim 19 wherein the first electrode comprises copper.

24. The semiconductor device recited in Claim 19 wherein the second and third electrodes each comprise a same one selected from the group consisting of:

tungsten;

tungsten silicide;

aluminum;

titanium; and

titanium nitride.

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25. The semiconductor device recited in Claim 19 wherein the second and third electrodes each include a plurality of conductive layers.